

VRRM	IF (TC≤135°C)	QC
650V	9A	18nC

Applications:

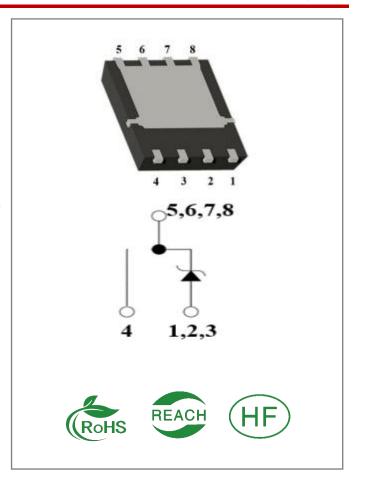
- Switch Mode Power Supplies
- Power Factor Correction
- Motor drive, PV Inverter, Wind Power Station

Features:

- Zero Reverse Recovery Current
- Zero Forward Recovery Voltage
- Positive Temperature Coefficient on VF
- Temperature-independent Switching
- 175°C Operating Junction Temperature

Benefits:

- Replace Bipolar with Unipolar Device
- Reduction of Heat Sink Size
- Parallel Devices Without Thermal Runaway
- Essentially No Switching Losses



Ordering Information

Part Number	Package	Marking	Packing	Qty.
RSS08065G	DFN5*6	RSS08065G	Tape&reel	5000 PCS



Maximum Ratings (TJ= 25°C unless otherwise specified)

Symbo I	Parameter	Valu e	Unit	Test Conditions	Not e
VRRM	M Repetitive Peak Reverse Voltage		V	TC = 25℃	
VRSM	Surge Peak Reverse Voltage	650	V	TC = 25℃	
VR	DC Blocking Voltage	650	V	TC = 25℃	
IF	Forward Current	19 9 8	А	TC ≤ 25°C TC ≤ 135°C TC ≤ 140°C	
IFSM	Non-Repetitive Forward Surge Current	87 72	А	TC = 25° C, tp = 10ms, Half Sine Wave TC = 110° C, tp = 10ms, Half Sine Wave	
IFRM	Repetitive Peak Forward Surge Current	68	Α	TC = 25° C, tp = 10ms, Half Sine Wave	
Ptot	Power Dissipation	63	W	TC = 25℃	
TC	Maximum Case Temperature	140	$^{\circ}$		
TJ,TST G	Operating Junction and Storage Temperature	-55 to17 5	$^{\circ}$		

Electrical Characteristics (TJ= 25°C unless otherwise specified)

Symbo I	Parameter	Тур.	Max	Unit	Test Conditions	Note
VF	Forward Voltage	1.39 1.74	1.6 -	V	IF = 8A, TJ = 25°C IF = 8A, TJ = 175°C	
IR	Reverse Current	6 12	60 -	μΑ	VR = 650V, TJ = 25°C VR = 650V, TJ = 175°C	
С	Total Capacitance	338 44 43	/	рF	VR = 1V, TJ = 25° C, f = 1MHz VR = 200V, TJ = 25° C, f = 1MHz VR = 400V, TJ = 25° C, f = 1MHz	
QC	Total Capacitive Charge	23	/	nC	VR =400V,	
Ec	Capacitance Stored Energy	3.7		uJ	VR =400V,	

Thermal Characteristics (TJ= 25°C unless otherwise specified)

Symbol	Parameter	Тур.	Unit	Note
RθJC	Thermal Resistance from Junction to Case	1.75	°C/W	



Typical Feature Curve

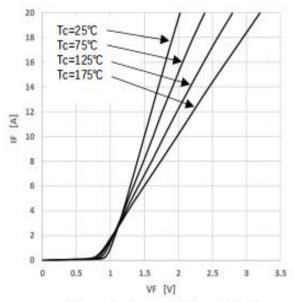


Figure 1 Forward Characteristics

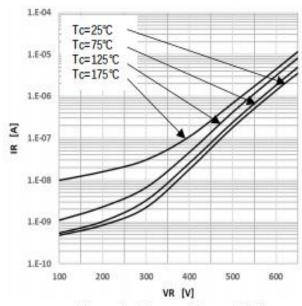


Figure 2 Reverse Characteristics

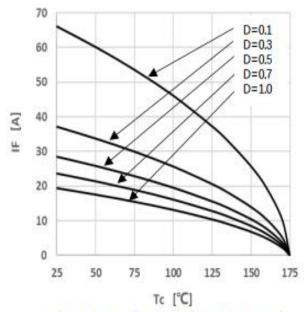


Figure 3 Peak Forward Current Derating

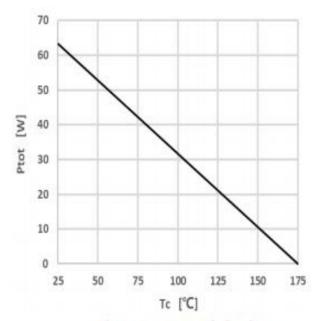


Figure 4 Power Dissipation

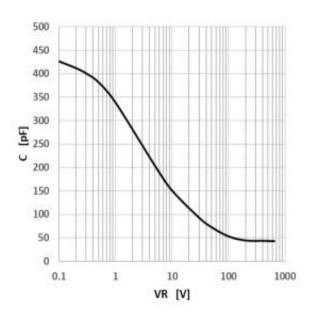


Figure 5 Capacitance vs. Reverse Voltage

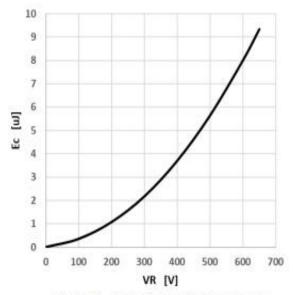


Figure 7 Capacitance Stored Energy

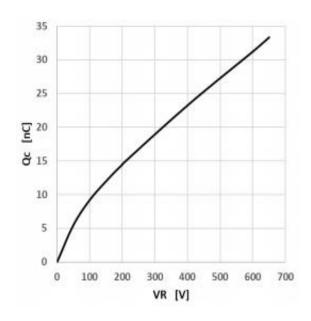


Figure 6 Capacitance Charge vs. Reverse Voltage

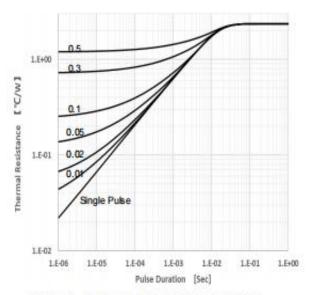
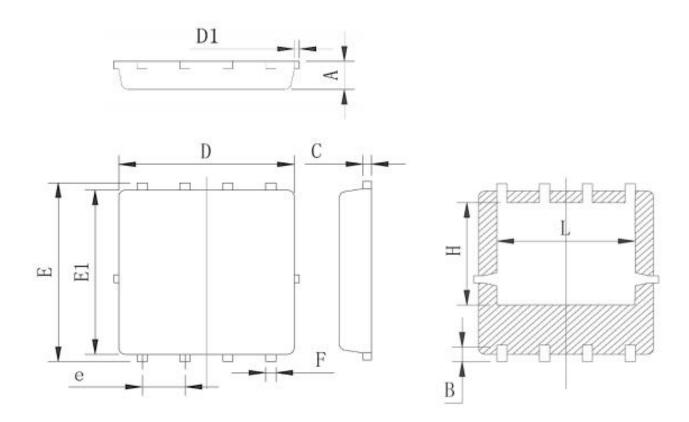


Figure 8 Transient Thermal Impedance



Package outline drawing(DFN5*6 Unit: mm)



Symbol	Min	Тур	Max
A	0.90	0.95	1.00
В	0.48	0.58	0.68
C	0.20	0.254	0.30
D	5.00	5.20	5.40
D1			0.15
E	5.90	6.05	6.20
E1	5.40	5.55	5.70
e	1.22	1.27	1.32
F	0.25	0.30	0.35
Н	3.27	3.47	3.67
L	3.80	4.00	4.20



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